

BR1001S

PRV : 100 Volts

Io : 6.0 Ampere

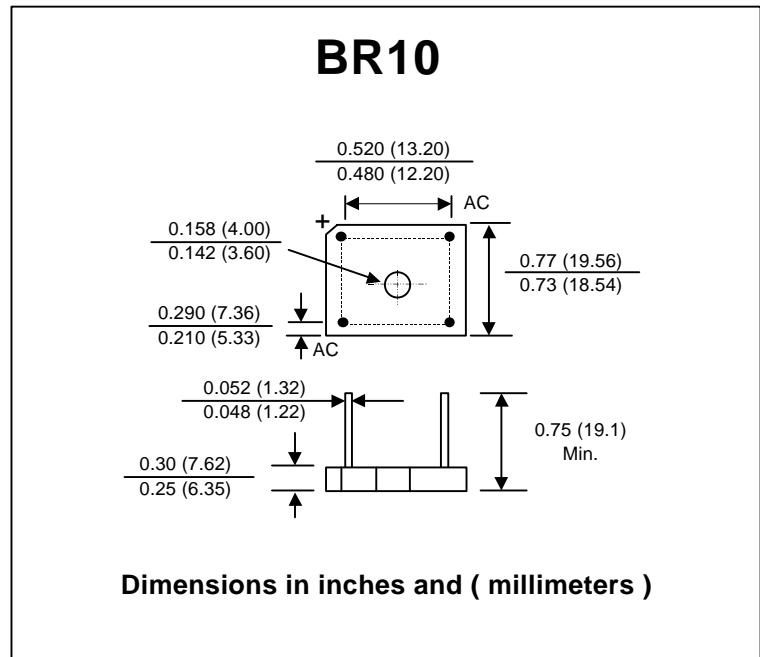
FEATURES :

- * High case dielectric strength
- * High surge current capability
- * High reliability
- * Low reverse current
- * Low forward voltage drop
- * Ideal for printed circuit board
- * **Pb / RoHS Free**

MECHANICAL DATA :

- * Case : Reliable low cost construction utilizing molded plastic technique
- * Epoxy : UL94V-O rate flame retardant
- * Lead : Axial lead solderable per MIL - STD 202 , Method 208 guaranteed
- * Polarity : Polarity symbols marked on case
- * Mounting position : Any
- * Weight : 6.1 grams

SILICON BRIDGE RECTIFIERS



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.
 Single phase, half wave, 50 Hz, resistive or inductive load.
 For capacitive load, derate current by 20%.

RATING	SYMBOL	VALUE	UNIT
Maximum Recurrent Peak Reverse Voltage	VRRM	100	V
Maximum RMS Voltage	VRMS	70	V
Maximum Reverse Voltage	VR	100	V
Maximum Average Forward Rectified Current Ta=40°C	IF(AV)	6.0	A
Maximum Peak Forward Surge Current Single half sine wave Superimposed on rated load (JEDEC Method)	IFSM	200	A
Maximum Forward Voltage drop per diode at If = 9.0 A	VF	1.0	V
Maximum Repetitive Peak Reverse Current	IRRM	10	µA
Typical Thermal Resistance at Junction to Ambient (Note 1)	RθJA	1.8	°C/W
Operating Junction Temperature Range	TJ	-40 to + 150	°C
Storage Temperature Range	Tstg	-40 to + 150	°C

Notes :

- 1) Thermal resistance from Junction to ambient with units mounted on a 100cm² x 1.5 t Al. plate.

RATING AND CHARACTERISTIC CURVES (BR1001S)

FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT

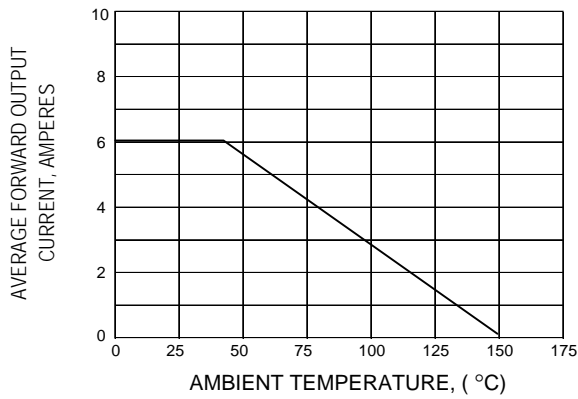


FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

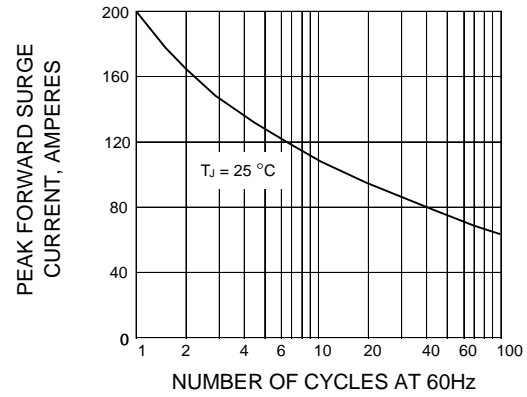


FIG.3 - TYPICAL FORWARD CHARACTERISTICS PER DIODE

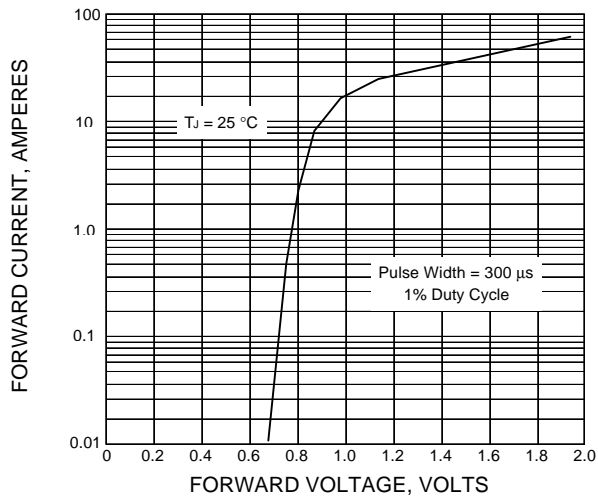


FIG.4 - TYPICAL REVERSE CHARACTERISTICS

